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(54) Title: PREPARATION OF HIGH PRESSURE BF₃/H₂ MIXTURES

(57) Abstract: Methods are described for filling gas mixture supply vessels with constituent gases to achieve precision compositions of the gas mixture, wherein the gas mixture comprises at least two constituent gases. Cascading fill techniques may be employed, involving flowing of gases from single source vessels to multiple target vessels, or from multiple source vessels to a single target vessel. The methods may be employed to form dopant gas mixtures, e.g., of boron trifluoride and hydrogen, for ion implantation applications.

